

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Claims 16 and 17 have been added.

Claim 13 has been amended as follows:

1 13. (Twice Amended) A semiconductor device having a semiconductor chip,
2 first electrodes formed on said semiconductor chip,
3 barrier metals formed on said first electrodes and having laminated structures, and
4 a plurality of second protruded electrodes, which serve as external connection terminals,
5 formed on said barrier metals, wherein said barrier metals comprising:
6 a lowermost conductive metal layer laminated on said first electrodes, said lowermost
7 conductive metal layer having a comparatively good joining property with said first electrodes;
8 an intermediate conductive metal layer laminated on said lowermost conductive metal
9 layer, said intermediate conductive metal layer comprising one or more layers and having a
10 comparatively good joining property with said lowermost conductive metal layer, said intermediate
11 conductive metal layer having at least one layer serving as a barrier layer for preventing said
12 protruded electrodes from diffusing into said intermediate conductive metal layer; and
13 an uppermost conductive metal layer laminated on said one or more intermediate
14 conductive metal layers, said uppermost conductive metal layer being made of a material which
15 easily alloys with the material of said intermediate conductive metal layers and which has good
16 resistance to oxidation.